

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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Electronics Make Possible

OPB610, OPB611, OPB620, OPB621

Features:

- Non-contact switching
- Printed circuit board mounting
- Enhanced signal to noise ratio
- PIN photodiode sensor for high speed (OPB611, OPB621)
- Lead centers: 0.275: (OPB61_) / 0.320" (OPB62_)



Description:

The **OPB610** and **OPB620** slotted optical switches consist of an infrared emitting diode and an NPN silicon phototransistor with an enhanced low current roll-off to improve contrast ratio and immunity to background irradiance.

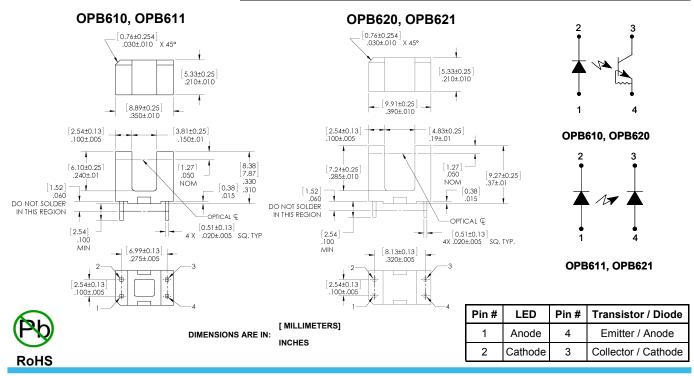
The **OPB611**, **OPB621** slotted optical switch consists of an infrared emitting diode and a PIN photodiode with a polysulfone housing that is opaque to visible light, but transmissive to infrared. The low t_r/t_f of the PIN photodiode is ideal for high-speed operation. The sensitivity to ambient radiation is minimized.

Custom electrical, wire and cabling and connectors are available. Contact your local representative or OPTEK for more information.

Applications:

- Non-contact reflective object sensor
- · Assembly line automation
- Machine automation
- Machine safety
- End of travel sensor
- Door sensor

Ordering Information										
Part Number	LED Peak Wavelength	Sensor	Slot Width / Depth	Aperture Emitter / Sensor	Lead Length / Spacing					
OPB610	890 nm	Rbe Transistor	0.150" / 0.240"	0.06" / 0.06"	0.100" / 0.275"					
OPB611		Diode								
OPB620		Rbe Transistor	0.400 / 0.205"		0.100" / 0.320"					
OPB621		Diode	0.190" / 0.285"							





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Power Dissipation⁽³⁾

Slotted Optical Switch



OPB610, OPB611, OPB620, OPB621

Electrical Specifications

Absolute Maximum Ratings (T_A=25°C unless otherwise noted)

Storage and Operating Temperature Range	-40°C to +100° C	
Lead Soldering Temperature [1/16 inch (1.6mm) from the case for 5 sec. with soldering iron] ⁽¹⁾	260° C	
put Diode	•	
Forward DC Current	50 mA	
Peak Forward Current (1 μs pulse width, 300 pps)	3 A	
Reverse DC Voltage	3 V	
Power Dissipation ⁽²⁾	100 mW	
utput Photodiode (OPB621)		
Reverse Breakdown Voltage	60 V	
Power Dissipation	100 mW	
utput Phototransistor (OPB610, OPB620)		
Collector-Emitter Voltage	24 V	
Emitter-Reverse Current	10 mA	
Collector DC Current	30 mA	

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200 mW



OPB610, OPB611, OPB620, OPB621

Electrical Specifications

Electrical Characteristics (T_A = 25°C unless otherwise noted)

SYMBOL	PARAMETER	MIN	TYP	MAX	UNITS	TEST CONDITIONS		
Input Diode (See OP240 for additional information)								
V _F	Forward Voltage OPB610, OPB620 OPB621		- -	1.6 1.45	V V	I _F = 10 mA I _F = 10 mA		
I _R	Reverse Current		-	100	μΑ	V _R = 3 V		
Output Phototransistor (OPB610, OPB620) (See OP505 for additional information)								
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	24	-	-	V	I _C = 100 μA		
BV _{ECO}	Emitter-Collector Breakdown Voltage	0.4	-	-	V	Ι _{CE} = 100 μΑ		
I _{CEO}	Collector-Emitter Dark Current	-	-	100	nA	V _{CE} = 5 V		
Output Photodiode (OPB611, OPB621) (See OP999 for additional information)								
I _D	Dark Current	-	-	65	nA	V _R = 30 V, E _E = 0 mW		
V _{(BR)R}	Reverse Breakdown Voltage	60	-	-	٧	IR = 100 μA, E _E = 0 mW		
V _F	Forward Voltage	-	-	1.0	V	I _F = 1 mA, E _E = 0 mW		
Combined								
V _{SAT}	Collector-Emitter Saturation Voltage OPB610, OPB620	-	-	0.4	V	I _F = 5 mA, I _C = 100 μA		
I _{C(ON)}	On-State Collector/Diode Current OPB610, OPB620 OPB611, OPB621	1 9	-	- 90	mA μA	$I_F = 5$ mA, $V_{CE} = 5$ V (gap unblocked) $V_R = 5$ V, $I_F = 20$ mA (gap unblocked)		

Notes:

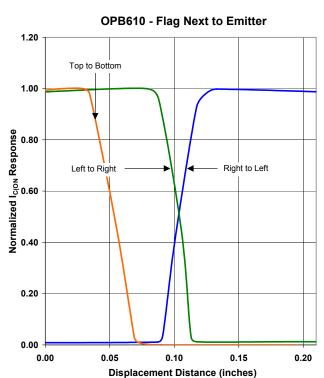
- RMA flux is recommended. Duration can be extended to 10 seconds maximum when flow soldering. A maximum of 20 grams force may be applied to leads when soldering.
- Derate linearly 1.33 mW/°C above 25 ° C.
- Derate linearly 2.0 mW/°C above 25 ° C.
- (2) (3) (4) Plastic body is soluble in chlorinated hydrocarbons and keytones. It is recommended that a trial exposure to flux & cleaning chemicals is performed to ensure sensor is not damaged.

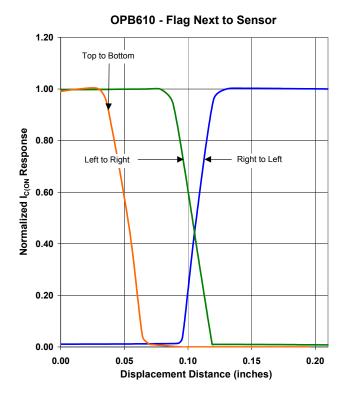
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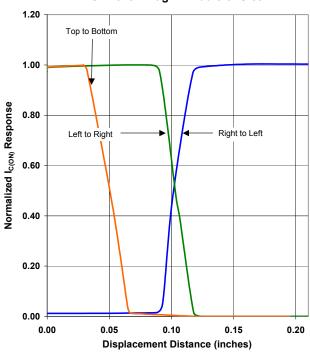
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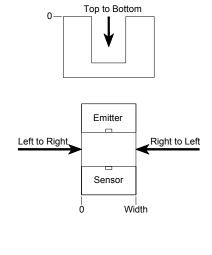
Performance





OPB610 - Flag in Middle of Slot





General Note

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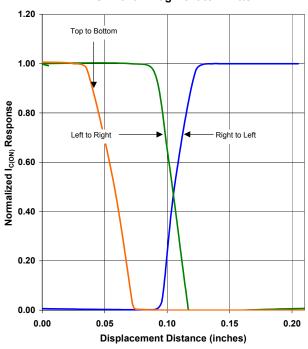




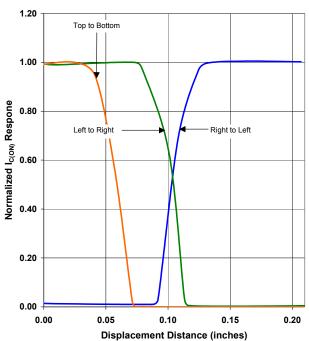
OPB610, OPB611, OPB620, OPB621

Performance

OPB620 - Flag Next to Emitter



OPB620 - Flag Next to Sensor



OPB620 - Flag in Middle of Slot

